

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L5	215	(varnish or paint or gloss or finish) near5 (halogen)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/04/10 08:07
L6	57149	((Curable or fixable or cure\$1 or curing or fix\$3) near5 (film\$1 or layer\$1 or strat\$2 or coat\$1 or coating\$1 or lamina or tier\$1 or sheet\$1)) with (polymer\$1 or plastic\$1 or resin\$1)	FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/04/10 08:08
L7	2	I5 and I6	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/04/10 08:23
S1	114753	(Multilayer or multi-layer or ((many or multiple or two or plural or multi\$1 or two) near3 ((monolayer\$1 or mono\$1layer\$1) or strat\$2 or level\$1))) with (circuit\$2 or chip\$1 or microchip or micro\$1chip or microcircuit or microprocessor\$1 or processor\$1 or semiconductor\$1 or semi\$1conductor\$1)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/31 11:13
S2	42650	(Multilayer or multi-layer or ((many or multiple or two or plural or multi\$1 or two) near3 ((monolayer\$1 or mono\$1layer\$1) or strat\$2 or level\$1))) with (circuit\$2 or chip\$1 or microchip or micro\$1chip or microcircuit or microprocessor\$1 or processor\$1 or semiconductor\$1 or semi\$1conductor\$1)	FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/31 11:15
S4	54836	(Coordinate\$1 or coordinating or complex or complex\$3 or chelate\$1 or chelat\$3) near5 metal\$1	FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/31 11:16
S7	39991	(hydrophilic or hydrophiliz\$3 or hydrophilic\$3 or hydrophilicat\$3) near5 (film\$1 or layer\$1 or strat\$2 or coat\$1 or coating\$1 or lamina or tier\$1 or sheet\$1 or surface\$1)	FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/31 11:17
S10	19	((ethylenediaminetetraacetic or edita or C10H16N2O8 or "C.sub.10.H.sub.16.N.sub.2.O.sub.8") with (copper or cu)) with (circuit or conductor or conductive)	FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/31 11:18
S20	56431	(hydrophilic or hydrophiliz\$3 or hydrophilic\$3 or hydrophilicat\$3 or water\$1soluble or water\$1miscible) near5 (film\$1 or layer\$1 or strat\$2 or coat\$1 or coating\$1 or lamina or tier\$1 or sheet\$1 or surface\$1)	FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/31 11:24

S21	81952	(hydrophilic or hydrophiliz\$3 or hydrophilic\$3 or hydrophilicat\$3 or water \$1soluble or water\$1miscible or potassium permanganate or kmno4 or "KMNO.sub.4") with (film\$1 or layer\$1 or strat\$2 or coat\$1 or coating\$1 or lamina\$4 or tier\$1 or sheet\$1 or surface \$1)	FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/31 11:26
S22	328	S4 and S7 and S21	FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/31 11:27
S23	178	S4 same S7 same S21	FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/31 11:27
S24	0	S23 and S10	FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/31 11:27
S25	0	S22 and S1	FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/31 11:32
S26	0	S10 and S1	FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/31 11:32
S27	6875359	(circuit\$2 or chip\$1 or microchip or micro \$1chip or microcircuit or microprocessor \$1 or processor\$1 or semiconductor\$1 or semi\$1conductor\$1)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/31 11:33
S28	19	S22 and S27	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/31 11:34
S29	8	S27 and S23	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/31 11:34
S30	18	S27 and S10	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/31 11:35
S32	21	((ethylenediaminetetraacetic or (ethylenediamine near2 (tetraacetic or tetra-acetic or tetra\$1acetic)) or edta or C10H16N2O8 or "C.sub.10.H.sub.16.N.sub.2.O.sub.8") with (copper or cu)) with (circuit or conductor or conductive)	FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/31 11:42
S33	85	((ethylenediaminetetraacetic or edta or C10H16N2O8 or "C.sub.10.H.sub.16.N.sub.2.O.sub.8") with (copper or cu)) with (circuit or conductor or conductive or (electroless near3 plat\$3))	FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/31 11:43

S34	31	S33 and S27	FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/31 11:54
S35	121385	((Multilayer or multi-layer or ((several or many or multiple or two or plural or multi \$1 or two) near3 ((monolayer\$1 or mono \$1layer\$1) or strat\$2 or level\$1 or lamina \$5))) with (circuit\$2 or chip\$1 or microchip or micro\$1chip or microcircuit or microprocessor\$1 or processor\$1 or semiconductor\$1 or semi\$1conductor\$1)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/31 12:09
S38	2	("0175824").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2008/03/31 13:02
S39	57100	((Curable or fixable or cure\$1 or curing or fix\$3) near5 (film\$1 or layer\$1 or strat \$2 or coat\$1 or coating\$1 or lamina or tier\$1 or sheet\$1)) with (polymer\$1 or plastic\$1 or resin\$1)	FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/31 13:27
S40	5343	S39 and S27	FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/31 13:29
S41	20	S39 and S27 and S4	FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/31 13:30
S45	73	wakizaka, yasuhiro.inv.	FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/31 13:37
S47	1	wakizawa, yasuhiro.inv.	US-PGPUB; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/31 13:39
S48	2	S45 and S4	FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/31 13:51
S49	0	S4 and I27	FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/31 13:56
S50	3274	S4 and S27	FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/31 13:56
S51	60	infiltrated layer	FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/31 14:12
S52	545	infiltrated near5 layer	FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/31 14:13

S55	29418	(nitrogen or N) near5 (heterocyclic or imidazole\$1 or pyrazole\$1 or triazole\$1 or triazine\$1)	FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/31 14:17
S57	926	S4 and S55	FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/31 14:18
S58	48	S57 and S27	FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/31 14:18
S59	960	S55 and S27	FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/31 14:21
S60	11	S55 and S27 and S39	FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/31 14:22
S61	11	S27 and S55 and smooth	FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/31 14:32
S62	1	S33 and S55	FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/31 16:56
S63	200280	(epoxy or maleimide or methacrylic or meth\$1acrylic or (diallyl near2 phthalate) or (alicyclic near2 olefin) or triazine or (aromatic near2 polyether) or benzocyclobutene or (cyanate near2 ester) or (liquid near2 crystal) or polyimide\$1) near3 (resin\$1 or plastic\$1 or polymer\$1)	FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/31 17:42
S64	8712	S63 and S39	FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/31 17:42
S65	62	S63 and S39 and S4	FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/31 17:44
S66	1474	S63 and S39 and S27	FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/31 17:44
S67	161	S63 and S39 and S1	FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/31 17:44

S68	202698	(epoxy or maleimide or methacrylic or methacrylic or (diallyl near2 phthalate) or (alicyclic near2 olefin) or triazine or (aromatic near2 polyether) or benzocyclobutene or (cyanate near2 ester) or (liquid near2 crystal) or polyimide\$1 or norbornene) near3 (resin \$1 or plastic\$1 or polymer\$1)	FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/31 17:49
S69	8754	S68 and S39	FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/31 17:50
S70	62	S68 and S39 and S4	FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/31 17:50
S71	161	S68 and S39 and S1	FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/31 17:51
S72	1476	S68 and S39 and S27	FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/31 17:51
S73	73	S69 and norbornene	FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/31 17:52
S74	0	S71 and norbornene	FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/31 17:52
S75	36	S1 and norbornene	FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/31 17:53
S76	235	S4 and norbornene	FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/31 17:54
S78	0	S39 and S33	FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/31 18:20
S79	82	S63 and edta	FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/31 18:20
S80	13	S63 and (edta with (copper or cu))	FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/31 18:21
S81	52290	(hydrophilic or hydrophilic\$3 or hydrophilic\$3 or hydrophilic\$3 or potassium permanganate or kmno4 or "KMNO.sub.4") with (film\$1 or layer\$1 or strat\$2 or coat\$1 or coating\$1 or lamina or tier\$1 or sheet\$1 or surface \$1)	FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/04/07 14:54

S82	666	(hydrophilic or hydrophiliz\$3 or hydrophilic\$3 or hydrophilicat\$3 or potassium permanganate or kmno4 or "KMNO.sub.4") with (((alkali or sodium) near3 hydroxide) or NaOH)	FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/04/07 14:56
S83	42686	(Multilayer or multi-layer or ((many or multiple or two or plural or multi\$1 or two) near3 ((monolayer\$1 or mono \$1layer\$1) or strat\$2 or level\$1))) with (circuit\$2 or chip\$1 or microchip or micro \$1chip or microcircuit or microprocessor \$1 or processor\$1 or semiconductor\$1 or semi\$1conductor\$1)	FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/04/07 14:57
S86	6884795	(circuit\$2 or chip\$1 or microchip or micro \$1chip or microcircuit or microprocessor \$1 or processor\$1 or semiconductor\$1 or semi\$1conductor\$1)	US-PG Pub; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/04/07 14:59
S87	34	S82 and S86	US-PG Pub; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/04/07 14:59
S88	595	(potassium permanganate or kmno4 or "KMNO.sub.4") with (film\$1 or layer\$1 or strat\$2 or coat\$1 or coating\$1 or lamina or tier\$1 or sheet\$1 or surface \$1)	FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/04/07 15:01
S89	296	(potassium permanganate or kmno4 or "KMNO.sub.4") with (((alkali or sodium) near3 hydroxide) or NaOH)	FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/04/07 15:01
S90	26	S86 and S89	FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/04/07 15:02
S91	1	("7056424").PN.	US-PG Pub; USPAT; USOCR	OR	OFF	2008/04/07 15:08
S92	1	("5104687").PN.	US-PG Pub; USPAT; USOCR	OR	OFF	2008/04/07 15:30
S93	54900	(Coordinate\$1 or coordinating or complex or complex\$3 or chelate\$1 or chelat\$3) near5 metal\$1	FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/04/07 15:51
S94	29445	(nitrogen or N) near5 (heterocyclic or imidazole\$1 or pyrazole\$1 or triazole\$1 or triazine\$1)	FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/04/07 15:51
S95	927	S93 and S94	FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/04/07 15:51
S96	40022	(hydrophilic or hydrophiliz\$3 or hydrophilic\$3 or hydrophilicat\$3) near5 (film\$1 or layer\$1 or strat\$2 or coat\$1 or coating\$1 or lamina or tier\$1 or sheet\$1 or surface\$1)	FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/04/07 15:54

S97	5	S96 and S93 and S94	FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/04/07 15:54
S98	328	S96 and S93	FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/04/07 15:55
S99	57149	((Curable or fixable or cure\$1 or curing or fix\$3) near5 (film\$1 or layer\$1 or strat\$2 or coat\$1 or coating\$1 or lamina or tier\$1 or sheet\$1)) with (polymer\$1 or plastic\$1 or resin\$1)	FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/04/07 15:56
S100	5	S96 and S93 and S99	FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/04/07 15:56
S101	9897	S99 and laminat\$3	FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/04/07 16:15
S102	1148	S99 and S86 and laminat\$3	FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/04/07 16:16
S103	201	S99 and S86 and laminat\$3 and S83	FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/04/07 16:17
S104	139	S99 and S86 and laminat\$3 and S83 and (insulat\$3 or dielectric)	FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/04/07 16:18
S106	119	S99 and S86 and (insulat\$3 or dielectric) and (varnish or glaze or paint)	FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/04/07 16:36
S109	1	S99 and S86 and (insulat\$3 or dielectric) and ((varnish or glaze or paint) near5 ((inner or inside) near3 (layer\$1 or strat\$2 or level\$1 or lamina\$5)))	FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/04/07 16:41
S110	19835	(electroless or non adj electrolytic or non-electrolytic) near3 (plate or plating)	FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/04/09 07:37
S111	121645	((Multilayer or multi-layer or ((several or many or multiple or two or plural or multi\$1 or two) near3 ((monolayer\$1 or mono\$1layer\$1) or strat\$2 or level\$1 or lamina\$5))) with (circuit\$2 or chip\$1 or microchip or micro\$1chip or microcircuit or microprocessor\$1 or processor\$1 or semiconductor\$1 or semi\$1conductor\$1)	US-PGRUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/04/09 07:39
S112	57149	((Curable or fixable or cure\$1 or curing or fix\$3) near5 (film\$1 or layer\$1 or strat\$2 or coat\$1 or coating\$1 or lamina or tier\$1 or sheet\$1)) with (polymer\$1 or plastic\$1 or resin\$1)	FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/04/09 07:39

S113	15	S111 and S110 and S112	US-PGRUB; USPAT; FFRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/04/09 07:39
S114	0	S111 and S110 and S112 and smooth	US-PGRUB; USPAT; FFRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/04/09 07:41
S115	7	S111 and S110 and smooth	US-PGRUB; USPAT; FFRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/04/09 07:49
S116	0	10-022634	US-PGRUB; USPAT; FFRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/04/09 07:55
S117	11	"10022634"	US-PGRUB; USPAT; FFRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/04/09 07:55
S118	3	S111 and ((Coordinate\$1 or coordinating or complex or complex\$3 or chelate\$1 or chelat\$3) near5 metal\$1) and smooth	FFRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/04/09 08:11
S119	417	S111 and ((Coordinate\$1 or coordinating or complex or complex\$3 or chelate\$1 or chelat\$3) near5 metal\$1) and smooth	US-PGRUB; USPAT; FFRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/04/09 08:12
S120	29445	(nitrogen or N) near5 (heterocyclic or imidazole\$1 or pyrazole\$1 or triazole\$1 or triazine\$1)	FFRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/04/09 08:21
S121	1	S111 and S120 and smooth	US-PGRUB; USPAT; FFRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/04/09 08:21
S122	1	S110 and S111 and S112 and S120	US-PGRUB; USPAT; FFRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/04/09 08:24
S123	1	"63211796"	JPO; DERWENT; IBM_TDB	ADJ	ON	2008/04/09 08:43
S128	232882	(resist\$1 or mask\$1 or masking\$1) near5 (pattern\$1 or patterning\$1 or template\$1 or design\$1)	US-PGRUB; USPAT; FFRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/04/09 10:05

S129	775	S128 and S110	US-PGRUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/04/09 10:06
S130	115000	((Multilayer or multi-layer or ((many or multiple or two or plural or multi\$1 or two) near3 ((monolayer\$1 or mono\$1layer\$1) or strat\$2 or level\$1))) with (circuit\$2 or chip\$1 or microchip or micro\$1chip or microcircuit or microprocessor\$1 or processor\$1 or semiconductor\$1 or semi\$1conductor\$1)	US-PGRUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/04/09 10:07
S131	12930	S128 and S130	US-PGRUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/04/09 10:07
S132	164	S131 and (CuCl2 or "CuCl.sub.2" or cupric chloride) and (hydrochloric acid or HCl)	US-PGRUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/04/09 10:09
S133	232882	(resist\$1 or mask\$1 or masking\$1) near5 (pattern\$1 or patterning\$1 or template\$1 or design\$1)	US-PGRUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/04/09 10:22
S134	115000	((Multilayer or multi-layer or ((many or multiple or two or plural or multi\$1 or two) near3 ((monolayer\$1 or mono\$1layer\$1) or strat\$2 or level\$1))) with (circuit\$2 or chip\$1 or microchip or micro\$1chip or microcircuit or microprocessor\$1 or processor\$1 or semiconductor\$1 or semi\$1conductor\$1)	US-PGRUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/04/09 10:22
S135	12930	S133 and S134	US-PGRUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/04/09 10:22
S136	164	S135 and (CuCl2 or "CuCl.sub.2" or cupric chloride) and (hydrochloric acid or HCl)	US-PGRUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/04/09 10:22
S144	4156887	(heat or (high near2 temperature) or oven or anneal\$3)	US-PGRUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/04/09 10:37
S145	18891	S133 same S144	US-PGRUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/04/09 10:39

S146	1416	(CuCl2 or "CuCl.sub.2" or cupric chloride) with (hydrochloric acid or HCl)	US-PGRUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/04/09 10:40
S147	12	S145 same S146	US-PGRUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/04/09 10:40
S148	36718	S134 and S144	US-PGRUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/04/09 10:42
S149	94	S148 and S146	US-PGRUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/04/09 10:43
S150	115000	((Multilayer or multi-layer or ((many or multiple or two or plural or multi\$1 or two) near3 ((monolayer\$1 or mono\$1layer\$1) or strat\$2 or level\$1)))) with (circuit\$2 or chip\$1 or microchip or micro\$1chip or microcircuit or microprocessor\$1 or processor\$1 or semiconductor\$1 or semi\$1conductor\$1)	US-PGRUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/04/09 11:08
S151	19905	S150 and (((two near3 side\$1) or (double near3 side\$1) or (both near3 side\$1)))	US-PGRUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/04/09 11:08
S152	79	S151 and S146	US-PGRUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/04/09 11:09
S154	10371	S151 and ((CuCl2 or "CuCl.sub.2" or cupric chloride) with (hydrochloric acid or HCl) or etch\$3)	US-PGRUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/04/09 11:11
S155	7462	S154 and S144	US-PGRUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/04/09 11:12
S156	382	S154 and S144 and "427".clas.	US-PGRUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/04/09 11:15
S157	262572	(resist\$1 or photo\$1resist or mask\$1 or masking\$1) near5 (pattern\$1 or patterning\$1 or template\$1 or design\$1)	US-PGRUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/04/09 11:17

S158	41	S133 same S146	US-PGRUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/04/09 11:18
S159	12	S133 same S146 same S144	US-PGRUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/04/09 11:18
S160	2	"7323093"	US-PGRUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/04/09 11:36
S161	85643	anneal\$3 and etch\$3	US-PGRUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/04/09 11:37
S162	51	S161 and S146	US-PGRUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/04/09 11:38
S163	155653	"427".clas.	US-PGRUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/04/09 12:05
S164	374759	"427".clas. or "216".clas. or "438".clas.	US-PGRUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/04/09 12:06
S165	121645	(Multilayer or multi-layer or ((several or many or multiple or two or plural or multi \$1 or two) near3 ((monolayer\$1 or mono \$1layer\$1) or strat\$2 or level\$1 or lamina \$5))) with (circuit\$2 or chip\$1 or microchip or micro\$1chip or microcircuit or microprocessor\$1 or processor\$1 or semiconductor\$1 or semi\$1conductor\$1)	US-PGRUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/04/09 12:07
S166	15412	S164 and S165	US-PGRUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/04/09 12:07
S170	39	wakizaka.inv. and multilayer circuit	US-PGRUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/04/09 15:03
S171	8	wakizaka.inv. and multilayer circuit	US-PGRUB	ADJ	ON	2008/04/09 15:07
S172	2	wakizawa.inv. and multilayer circuit	US-PGRUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/04/09 15:11

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